

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional blocking voltage capability, high current inrush capability and high thermal cycling performance.

2. Features and benefits

- AC power control
- High bidirectional blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

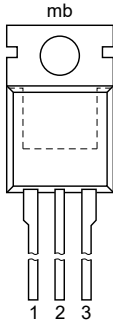

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 101\text{ °C}$	-	-	16	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 101\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	25	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	300	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	330	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	-	5	35	mA
Dynamic characteristics						

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	500	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p style="text-align: center;">TO-220AB (SOT78)</p>	
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT145-800R	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 101\text{ }^{\circ}\text{C}$	-	16	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 101\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	25	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	300	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	330	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	450	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	200	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	5	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

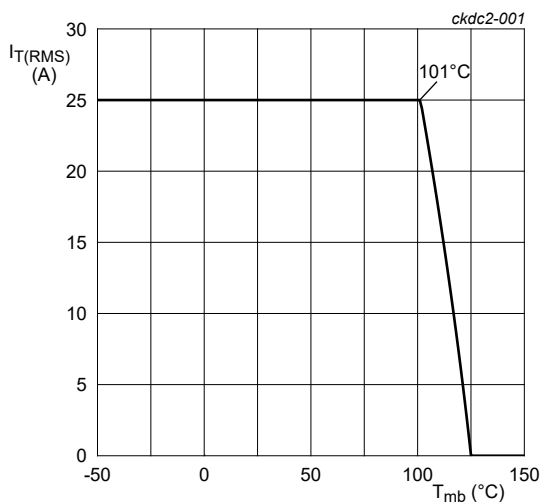
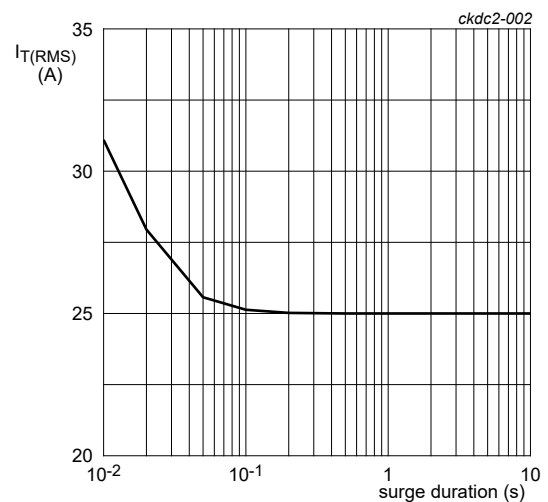


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} = 101\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

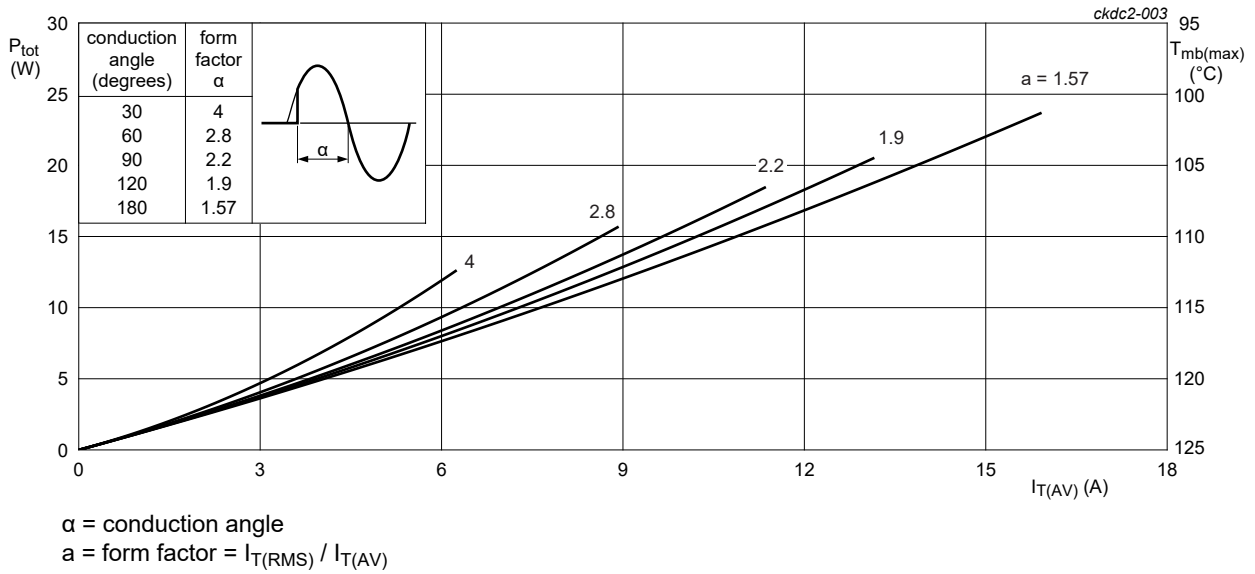


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

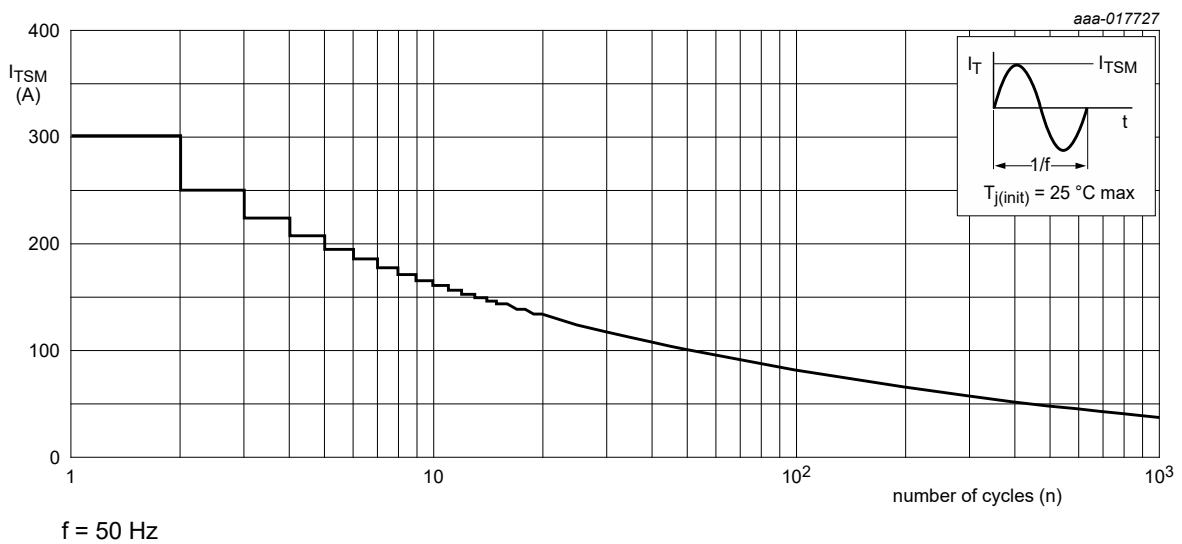


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	5	35	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	25	80	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	20	60	mA
V_T	on-state voltage	$I_T = 30\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.1	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.6	1	V
		$V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.2	1	mA
I_R	reverse current	$V_R = 800\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.2	1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	500	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ mA}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$	-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{TM} = 50\text{ A}$; $V_R = 25\text{ V}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; ($V_{DM} = 67\%$ of V_{DRM})	-	70	-	μs

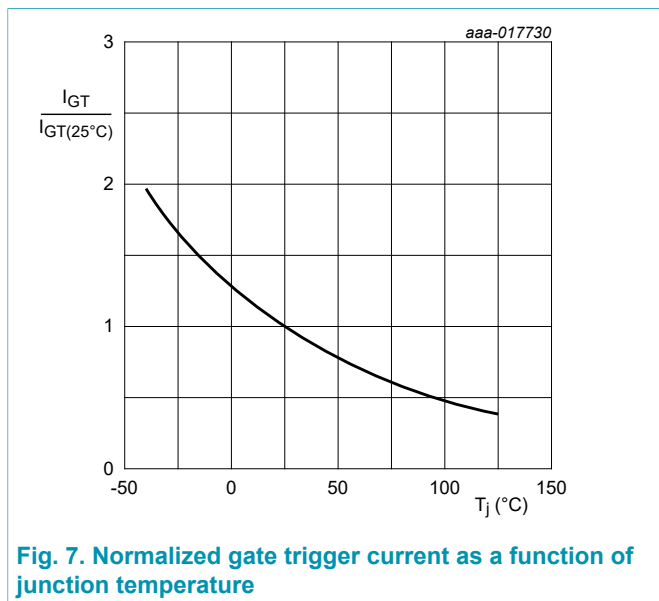


Fig. 7. Normalized gate trigger current as a function of junction temperature

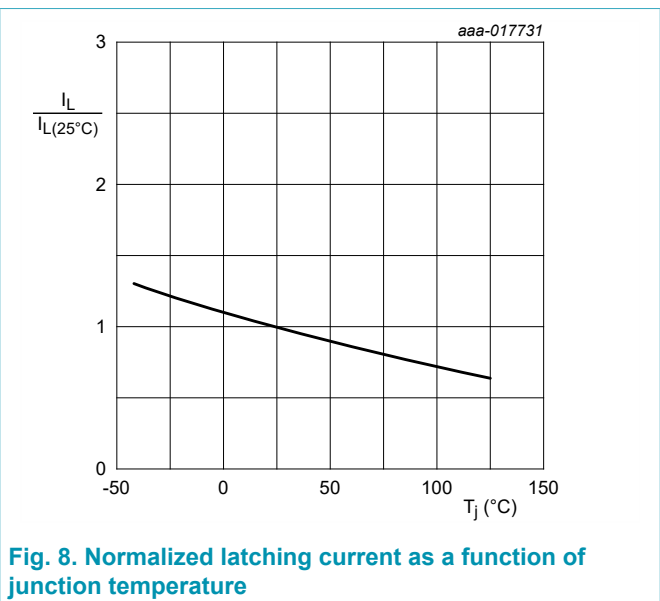


Fig. 8. Normalized latching current as a function of junction temperature

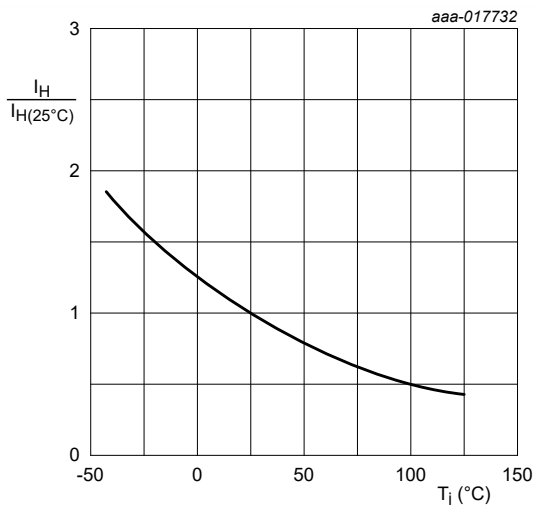
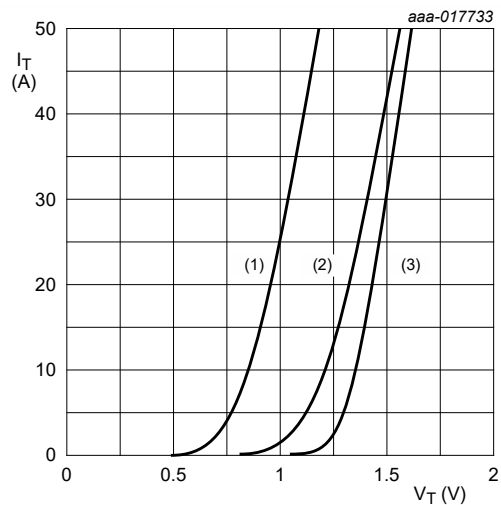


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.145 \text{ V}; R_s = 0.009 \Omega$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

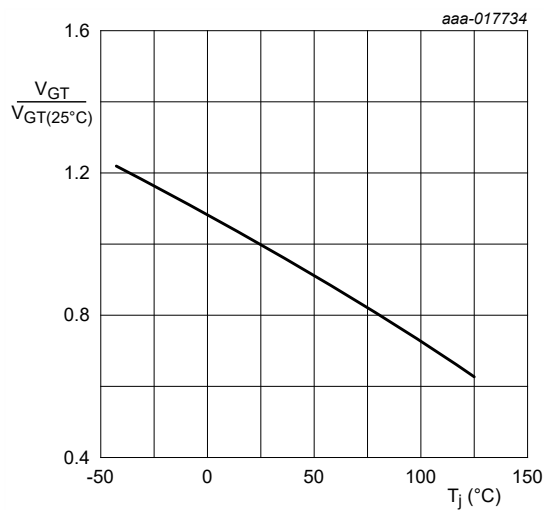
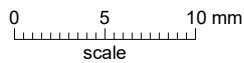
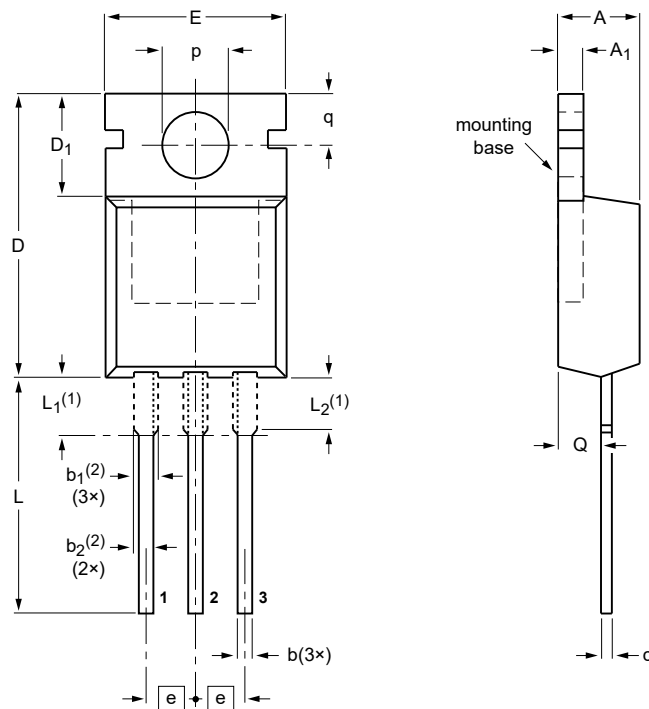


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

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